TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

TA2029FNG, TA2029NG

FM F / E + AM / FM IF + PW IC

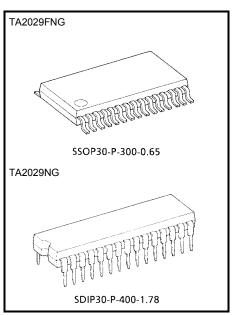
For Digital Tuning System

The TA2029FNG / NG are AM / FM single chip radio system ICs which are designed for monaural radio.

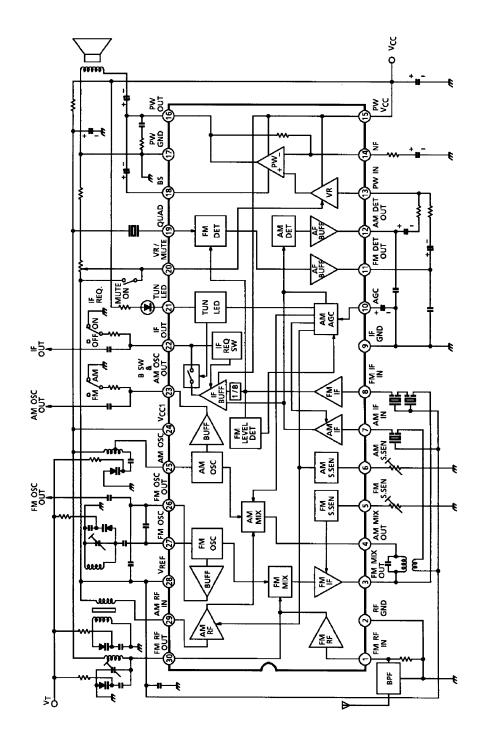
These ICs have many functions and can be used for digital tuning system.

Features

- Built-in FM F / E, AM / FM IF, electronic volume and power amplifier.
- Suitable for combination with digital tuning system which has IF counter.
 - AM / FM IF output for IF counter. FM: 1.3375MHz (1 / 8 IF) AM: 450kHz
 - AM / FM oscillation buffer outputs.
 - Auto stop sensitivity at the searching mode is adjustable by external resistances. (pin (5), pin(6))
- Adjustment-free type FM detector.
- Built-in AF power amplifier, electronic volume and audio muting circuits.
- Detector outputs FM / AM are independent each other.
- P_o = 100mW (typ.), THD = 10% (FN: 3V / 8Ω)
 P_o = 500mW (typ.), THD = 10% (N: 6V / 8Ω)
- Operating supply voltage range : V_{CC} = 1.8~8V (Ta = 25°C)



Weight SSOP30-P-300-0.65: 0.17g (typ.) SDIP30-P-400-1.78: 2.2g (typ.)



2004-10-12

BLOCK DIAGRAM

Explanation Of Terminal (Note: Ta = 25°C, V_{CC} = 3V, at no signal)

Pin	Characteristic	Internal Circuit	DC Voltage (V) (typ.)		
No.			AM	FM	
1	FM RF in FM RF input terminal	FM-RF OUT 30	0	0.7	
2	RF GND (GND of RF stage)	_	0	0	
3	FM mix out Ceramic filter is connected. Recommendation SFE10.7MA5L (murata MFG. Co., LTD)	V _{CC1} 24 MIX 300 Ω 4 270 Ω 3 RF GND 2	2.3	1.8	
4	AM mix out	Vcc1 24 4 MIX RF GND 2	2.3	1.8	
5	FM S. SEN Adjustable for FM IF output sensitivity by external resistor.	V _{CC1} 22	0	0.3	
6	AM S. SEN Adjustable for AM IF output sensitivity by external resistor.	V _{CC1} 24	0.3	0	

TA2029FNG/NG

Pin	Characteristic	Internal Circuit	DC Voltage (V) (typ.)		
No.			AM	FM	
7	AM IF in	Vref 28 3 kΩ 7 RF GND 2	1.22	1.2	
8	FM IF in	V _{CC1} 22 G B IF GND 9	3.0	3.0	
9	IF GDN (GDN of AM / FM IF)	_	0	0	
10	AGC (AM AGC) Capacitor is connected.	V _{CC1} 24 IF GND 3	0	0	
11	FM DET out FM detector output terminal.	QUAD QUAD QUAD (1) (1) (1) (1) (1) (1) (1) (1) (1) (1)	_	1.2	
12	AM DET out AM detector output terminal.	24 V _{CC1}	0.5	1.2	

Pin	Characteristic	Internal Circuit	DC Voli (ty	age (V)
No.			AM	FM
13	PW in	13 ^{20 kΩ} ¹³ ^c t t t t t t t t t t t t t t t t t t t	0	0
14	NF Capacitor is connected.	PW V _{CC}	0.8	0.8
15	PW V _{CC} (V _{CC} of PW and buffer amplifier for IF counter)	╡	3.0	3.0
16	PW out		1.6	1.6
17	PW GND (GND of PW)		0	0
18	BS Capacitor is connected.	IF GND 3 (4) PW GND	3.0	3.0
19	QUAD FM QUAD detector ceramic discriminator is connected recommendation CDA10.7MG36. (Murat MFG. Co., LTD)	Vcc1 23	2.5	2.3
20	 MUTE / VR Variable resistor for electronic volume control is connected. Mute terminal V₂₀: V_{ref} → mute on 	PW V _{CC} (1) PW V _{CC} (1) PW PW PW PW PW PW PW	_	_
21	Tun LED	2 V _{CC1} 2 V _{CC1} 2 V _{CC1} 3 IF GND	_	_

Pin	Characteristic	Internal Circuit	DC Voltage (V) (typ.)			
No.			AM	FM		
22	IF out IF output terminal pin (22) connects with GND by resistor \rightarrow come out pin (22): Open \rightarrow non output	PW Vcc 13 22 Wcc1 1F GND 9	2.5	2.5		
23	AM OSC out / band SW AM oscillation buffer output terminal. Bias terminal for AM / FM switch circuit. Pin (23) connects with GND by resistor → AM mode pin (23): Open → FM mode	23 Vcc1 OSC OSC OSC OSC OSC OSC OSC OSC	1.7	2.5		
24	V _{CC1} (V _{CC} of RF stage)	_	3.0	3.0		
25	AM OSC AM OSC tank circuit is connected.	Buff CC1 CC1 CC1 CC1 CC1 CC1 CC1 C	3.0	3.0		
26	FM OSC out Capacitor is connected between pin (26) and pin (27) shown in the right figure.		0.7	0.5		
27	FM OSC FM OSC tank circuit is connected shown in the right figure.		1.22	1.15		
28	V _{ref} regulator voltage output terminal V _{ref} = 1.2V (typ.): FM mode 1.22V (typ.): AM mode	V _{CC1} 24	1.22	1.2		

Pin No.	Characteristic	Internal Circuit	DC Voltage (V) (typ.)		
NU.			AM	FM	
29	AM RF in AM RF input terminal.	Vref (2) (2) (2) (2) (3) (4) (4) (4) (4) (4) (4) (4) (4) (4) (4	1.22	1.2	
30	FM RF out FM RF tank circuit is connected.	Cf. pin (1)	3.0	3.0	

Maximum Ratings (Ta = 25°C)

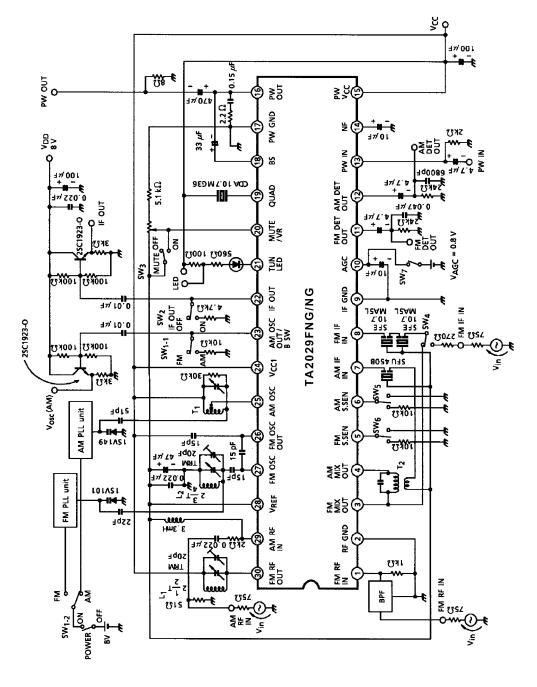
Characte	ristic	Symbol	Rating	Unit	
Supply voltage		V _{CC}	9	V	
Power dissipation	TA2029FNG	PD	500	mW	
Fower dissipation	TA2029NG	(Note)	1500		
Operating temperatur	e	T _{opr}	-25~75	°C	
Storage temperature		T _{stg}	-55~150	°C	

(Note): Derated above 25°C in the proportion of 4.8mW / °C for TA2029FNG and 12mW / °C for TA2029NG.

Electrical Characteristics Unless Otherwise Specified, Ta = 25°C, V_{CC} = 3V, SW₂: Off, SW₃: Off, SW₇ = Off F / E: f = 83MHz, f_m = 1kHz FM IF: f = 10.7MHz, Δf = ±22.5kHz, f_m = 1kHz AM: f = 1005kHz, MOD = 30%, f_m = 1kHz

Characteristic		Symbol	Test Cir– cuit	Test (Condition	Min.	Тур.	Max.	Unit	
		I _{CCQ} (FM)	1		Power amp: Off	_	11.5	16.0		
Supply current			I _{CC} (FM)	1	FM mode V _{in} = 0	Power amp: On SW ₂ : On, SW ₇ : On	_	18.0	25.0	mA
Ouppi	younon		I _{CCQ} (AM)	1	AM mode	Power amp: Off	_	7.5	11.0	
			I _{CC} (AM)	1	V _{in} = 0	Power amp: On SW ₂ : On, SW ₇ : On	_	17.0	24.0	
	Input limiting voltage)	V _{in (lim)}	1	–3dB limiting			12	_	dBµV EMF
F/E	Quiescent sensitivity		QS		S / N = 30dB			15	_	dBµV EMF
	Local OSC s voltage	stop	V _{stop} (FM)	2	V _{in} = 0		_	1.35	_	V
	Local OSC to output voltage		V _{osc (buff)}	2	f _{osc} = 108MHz		_	130	—	mV _{rms}
	Input limiting voltage		V _{in (lim)} IF	1	-3dB limiting		39	44	49	dBµV EMF
	Recovered output voltage		V _{OD}	1	V _{in} = 80dBµV EMF		55	80	110	mV _{rms}
	Signal to noise ratio		S / N	1	V _{in} = 80dBµV EMF		_	70	_	dB
	Total harmonic distortion		THD	1	V _{in} = 80dBµV EMF		_	0.4	_	%
	AM rejection	i ratio	AMR	1	V _{in} = 80dBµV EMF		-	48	—	dB
FM	LED on sens	sitivity	VL	1	I _L = 1mA		40	45	50	dBµV EMF
	IF count output frequency	1 / 8 IF	f1 / 8 IF (FM)	1	SW ₂ : On, V _{in} = 80dBµV	SW ₂ : On, V _{in} = 80dBµV EMF		1.3375	1.3377	MHz
	IF count output voltage	1 / 8 IF	V1 / 8 IF (FM)	1	SW ₂ : On, V _{in} = 80dBµV	SW ₂ : On, V _{in} = 80dBµV EMF		200	_	mV _{rms}
	IF count out	IF count output		1	SW ₆ : 10kΩ		_	48	_	dBµV
	sensitivity		IF _{sens} (FM)2	1	SW ₆ : 0Ω		_	68	—	EMF
	Pin (11) out resistance	out	R ₁₁	1	_		—	1	_	kΩ

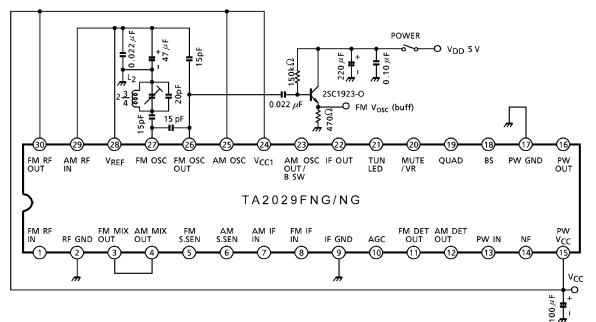
	Characteristic	Symbol	Test Cir– cuit	Test Condition	Min.	Тур.	Max.	Unit
	Gain	Gv	1	V _{in} = 26dBµV EMF	20	45	80	mV _{rms}
	Recovered output voltage	V _{OD}	1	V _{in} = 60dBµV EMF	50	75	100	mV _{rms}
	Signal to noise ratio	S / N	1	V _{in} = 60dBµV EMF	-	42	—	dB
	Total harmonic distortion	THD	1	V _{in} = 60dBµV EMF		1.0	—	%
AM	LED on sensitivity	VL	1	I _L = 1mA	24	29	34	dBµV EMF
	Local OSC buff. Output voltage	V _{osc} (AM)	1	f _{osc} = 1455kHz	80	140	—	mV _{rms}
	IF count output voltage	V _{IF} (AM)	1	SW ₂ : On, V _{in} = 60dBµV EMF	110	200	—	mV _{ms}
	IF count output sensitivity	IF _{SENS} (AM) 1	1	SW ₅ : 10kΩ		29	—	dBµV
		IF _{SENS} (AM) 2		SW ₅ : 0Ω	-	45		EMF
	Pin (12) output resistance	R ₁₂	1	_		5	—	kΩ
	Voltage gain	GV	1	f = 1kHz, R _L = 8Ω, V _o = 0.775V _{rms} , SW ₇ : On	27	30	33	dB
	Output power	P _{o1}	1	f = 1kHz, R _L = 8Ω, THD = 10%, SW ₇ : On	70	100	_	
PW		P _{o2}	1	V _{CC} = 6V, f = 1kHz, R _L = 8Ω, THD = 10%, SW ₇ : On	350	500	_	mW
ΓVV	Total harmonic distortion	THD	1	f = 1kHz, R _L = 8Ω, P _o = 50mW, SW ₇ : On	_	0.6	1.5	%
	Output noise voltage	V _{no}	1	R _g = 10kΩ, R _L = 8Ω, SW ₇ : On BPF = 30Hz~20kHz	_	0.45	_	mV _{rms}
	Muting attenuation	ATT	1	$V_0 = 0.775V_{rms}$ SW ₃ : Off \rightarrow on, SW ₇ : On	65	77	_	dB



TEST CIRCUIT 1

TA2029FNG/NG-10

TEST CIRCUIT 2



Coil Data

Test L C _o		-	Turns					Wire	5.4		
Coil No.	Frequency	(µH)	(pF)	Qo	1–2	2–3	1–3	1-4	4–6	(mm _φ)	Ref.
L ₁ FM RF	100MHz			100	I		I	$2\frac{1}{2}$	_	0.5 UEW	(S) 53T-037-202
L ₂ FM OSC	100MHz			100			$2\frac{3}{4}$	_	_	0.5 UEW	(S) 0258–244
T ₁ AM OSC	796kHz	288	_	115	13	73	_	—	—	0.08 UEW	(S) 4147–1356–038
T ₂ AM IFT	455kHz		180	120		-	180	—	15	0.08 UEW	(S) 2150–2162–165

(S) Sumida electric co., LTD

L₁ : FM RF

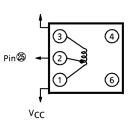
L₂ : FM OSC

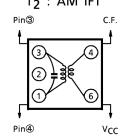
T₁ : AM OSC

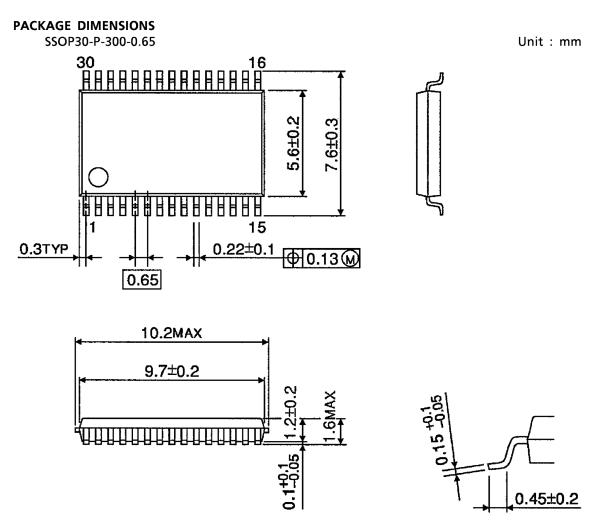
T₂ : AM IFT









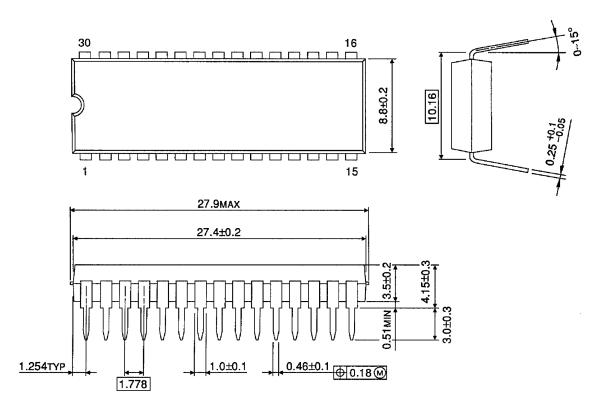


Weight: 0.17g (typ.)



PACKAGE DIMENSIONS SDIP30-P-400-1.78

Unit : mm



Weight: 2.2g (typ.)

```
Solderability

(1) Use of Sn-63Pb solder Bath

solder bath temperature = 230°C
dipping time = 5 seconds
the number of times = once
use of R-type flux

(2) Use of Sn-3.0Ag-0.5Cu solder Bath

solder bath temperature = 245°C
dipping time = 5 seconds
the number of times = once
use of R-type flux
```

About solderability, following conditions were confirmed

RESTRICTIONS ON PRODUCT USE

030619EBA

- The information contained herein is subject to change without notice.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of TOSHIBA or others.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor
 devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical
 stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of
 safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of
 such TOSHIBA products could cause loss of human life, bodily injury or damage to property.

In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..

- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- TOSHIBA products should not be embedded to the downstream products which are prohibited to be produced and sold, under any law and regulations.